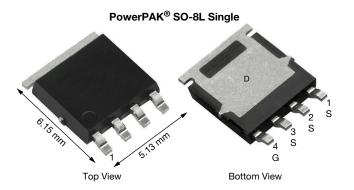
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Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY			
V _{DS} (V)	40		
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.00300		
I _D (A)	60		
Configuration	Single		
Package	PowerPAK SO-8L		

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

N-Channel MOSFET



COMPLIANT HALOGEN

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	otherwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current ^a	T _C = 25 °C		60		
	T _C = 125 °C	I _D	60		
Continuous Source Current (Diode conduction) ^a		I _S	60	А	
Pulsed Drain Current ^b		I _{DM}	150		
Single Pulse Avalanche Current		I _{AS}	45		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	101	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	P	68	W	
	T _C = 125 °C	P _D	22		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°O	
Soldering Recommendations (Peak temperature) d, e		· · · · ·	260	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB mount ^c	R _{thJA}	68	°C/W	
Junction-to-Case (Drain)		R _{thJC}	2.2	0/10	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static		1		<u> </u>	1		<u></u>	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		40	-	-	N	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		3.0	3.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A	-	0.00245	0.00300	Ω	
		V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.00440		
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.00520		
Forward Transconductance b	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		-	67	-	S	
Dynamic ^b	-	·						
Input Capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	3850	5000	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	2300	3050		
Reverse Transfer Capacitance	C _{rss}			-	70	100		
Total Gate Charge ^c	Qg		V _{DS} = 20 V, I _D = 5 A	-	67	105	nC	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V		-	19	-		
Gate-Drain Charge ^c	Q _{gd}]		-	9	-		
Gate Resistance	R _g	f = 1 MHz		0.24	0.49	0.75	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	18	30		
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{\text{L}} = 4 \Omega$ $\text{I}_{\text{D}} \cong 5 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		-	5	10	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	30	50		
Fall Time ^c	t _f			-	15	25		
Source-Drain Diode Ratings and Cha	racteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	150	Α	
Forward Voltage	V _{SD}	I _F = 15 A, V _{GS} = 0		-	0.81	1.20	V	
	•	4		•	•		•	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

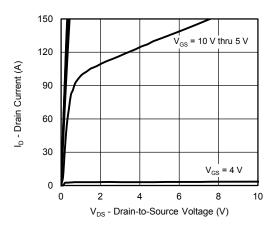
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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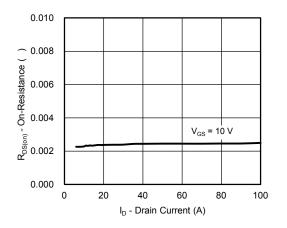


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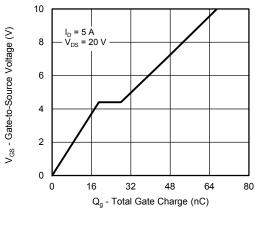
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



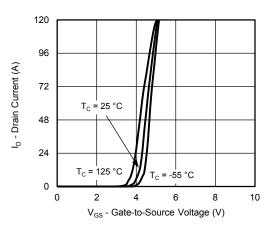
Output Characteristics



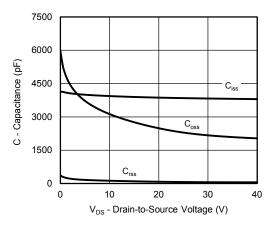
On-Resistance vs. Drain Current



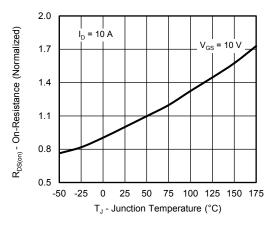
Gate Charge



Transfer Characteristics



Capacitance



On-Resistance vs. Junction Temperature

S16-1488-Rev. A, 01-Aug-16

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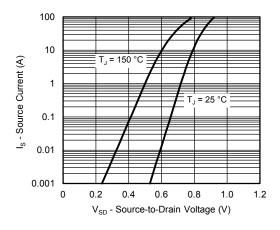
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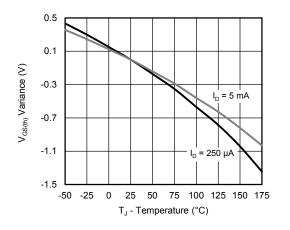
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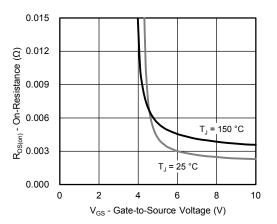
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



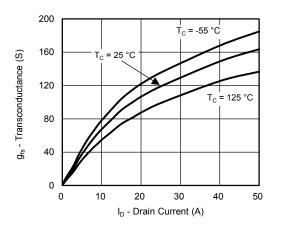
Source Drain Diode Forward Voltage



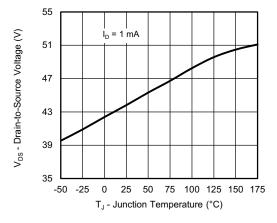
Threshold Voltage



On-Resistance vs. Gate-to Source Voltage



Transconductance



Drain Source Breakdown vs. Junction Temperature

4

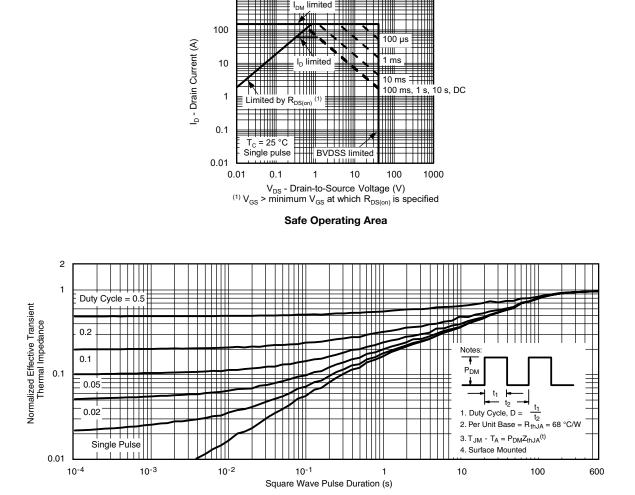
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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

1000



Normalized Thermal Transient Impedance, Junction-to-Ambient

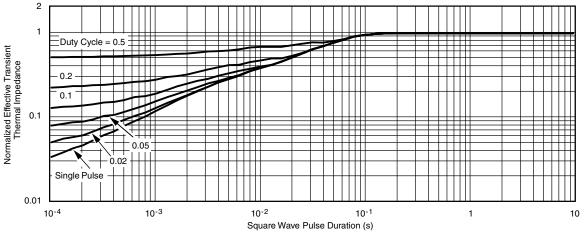


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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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